

## NTTFSSCH1D3N04XL

# MOSFET - Power, Single, N-Channel, Source Down Dual Cool 33, WDFN9, 40V, 1.3mΩ, 207A

## Product Overview

For complete documentation, see the data sheet.

The latest 40V logic gate level power MOSFET technology with best-in-class Figure-of-Merit for switching application. Lower on-resistance and less output capacitance can reduce the conduction and switching loss to accomplish higher efficiency requirement. smaller peak reverse recovery current with good softness behavior can perform lower voltage spike with better EMI performance.

This product is an improved 3x3 source-down Dual cool GEN2 package product, this has better thermal performance than previous 3x3 source down dual cool package with high thermal conductivity mold compound to achieve TC-55°C to +150°C

## Features

- Ultra Low R<sub>ds(on)</sub> to Improve System Efficiency
- Low Q<sub>g</sub> and Capacitance to Minimize Driving and Switching Losses
- Excellent Thermal Conduction by Advanced SourceDown Center Gate DualCooling Package Technology (3.3x3.3mm)
- Board level reliability (BLRT testing): 1000cycle with -40 to 125, 10min. dwell, 20/min, 6layers 2.35T
- These Devices are PbFree, HalogenFree/BFRFree and are RoHS Compliant

## Applications

- High Switching Frequency DC-DC Conversion
- Synchronous Rectifier

## End Products

- Cloud system
- Datacenter / IBC
- Power Supply Unit